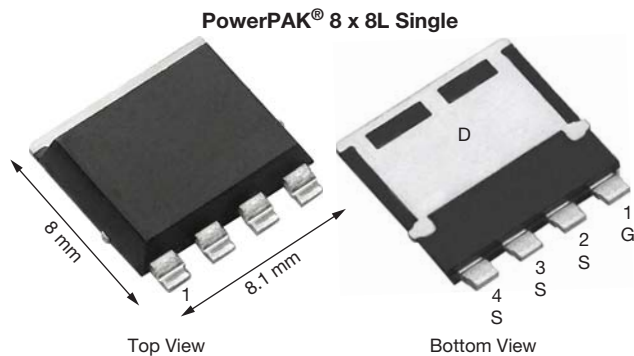


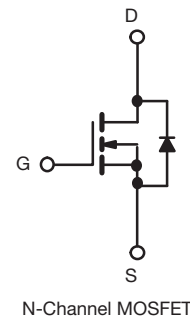
## Automotive N-Channel 40 V (D-S) 175 °C MOSFET



### FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>G</sub> and UIS tested
- Fully lead (Pb)-free device
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

| PRODUCT SUMMARY                                    |                 |
|--|-----------------|
| V <sub>DS</sub> (V)                                | 40              |
| R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 10 V  | 0.0012          |
| R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 4.5 V | 0.0015          |
| I <sub>D</sub> (A)                                 | 200             |
| Configuration                                      | Single          |
| Package  | PowerPAK 8 x 8L |



| ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted) |                                   |                                     |      |
|---|-----------------------------------|-------------------------------------|------|
| PARAMETER   | SYMBOL                            | LIMIT                               | UNIT |
| Drain-source voltage  | V <sub>DS</sub>                   | 40                                  | V    |
| Gate-source voltage   | V <sub>GS</sub>                   | ± 20                                |      |
| Continuous drain current  | I <sub>D</sub>                    | T <sub>C</sub> = 25 °C <sup>a</sup> | 200  |
|   |                                   | T <sub>C</sub> = 125 °C             | 141  |
| Continuous source current (diode conduction)                              | I <sub>S</sub>                    | 136                                 | A    |
| Pulsed drain current <sup>b</sup>   | I <sub>DM</sub>                   | 600                                 |      |
| Single pulse avalanche current  | I <sub>AS</sub>                   | 50                                  |      |
| Single pulse avalanche energy   | E <sub>AS</sub>                   | 125                                 | mJ   |
| Maximum power dissipation   | P <sub>D</sub>                    | T <sub>C</sub> = 25 °C              | 150  |
|   |                                   | T <sub>C</sub> = 125 °C             | 50   |
| Operating junction and storage temperature range                          | T <sub>J</sub> , T <sub>stg</sub> | -55 to +175                         | °C   |
| Soldering recommendations (peak temperature) <sup>d, e</sup>              |                                   | 260                                 |      |

| THERMAL RESISTANCE RATINGS |                   |       |      |
|----------------------------|-------------------|-------|------|
| PARAMETER                  | SYMBOL            | LIMIT | UNIT |
| Junction-to-ambient        | R <sub>thJA</sub> | 50    | °C/W |
| Junction-to-case (drain)   | R <sub>thJC</sub> | 1     |      |

### Notes

- Package limited
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



| SPECIFICATIONS (T <sub>C</sub> = 25 °C, unless otherwise noted)   |                     |  |   |      |        |        |    |
|---|---------------------|--|---|------|--------|--------|----|
| PARAMETER   | SYMBOL              | TEST CONDITIONS  | MIN.  | TYP. | MAX.   | UNIT   |    |
| <b>Static</b>   |                     |  |   |      |        |        |    |
| Drain-source breakdown voltage                                    | V <sub>DS</sub>     | V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA   | 40  | -    | -      | V      |    |
| Gate-source threshold voltage                                     | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA  | 1.5   | 2    | 2.5    |        |    |
| Gate-source leakage   | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V  | -   | -    | ± 100  | nA     |    |
| Zero gate voltage drain current                                   | I <sub>DSS</sub>    | V <sub>GS</sub> = 0 V  | V <sub>DS</sub> = 40 V                          | -    | -      | 1      | μA |
|   |                     | V <sub>GS</sub> = 0 V  | V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C | -    | -      | 50     |    |
|   |                     | V <sub>GS</sub> = 0 V  | V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C | -    | -      | 500    |    |
| On-state drain current <sup>a</sup>                               | I <sub>D(on)</sub>  | V <sub>GS</sub> = 10 V   | V <sub>DS</sub> ≥ 5 V                           | 100  | -      | -      | A  |
| Drain-source on-state resistance <sup>a</sup>                     | R <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V   | I <sub>D</sub> = 20 A                           | -    | 0.0009 | 0.0012 | Ω  |
|   |                     | V <sub>GS</sub> = 4.5 V  | I <sub>D</sub> = 10 A                           | -    | 0.0011 | 0.0015 |    |
|   |                     | V <sub>GS</sub> = 10 V   | I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C  | -    | -      | 0.0018 |    |
|   |                     | V <sub>GS</sub> = 10 V   | I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C  | -    | -      | 0.0022 |    |
| Forward transconductance <sup>b</sup>                             | g <sub>fs</sub>     | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A  | -   | 122  | -      | S      |    |
| <b>Dynamic<sup>b</sup></b>  |                     |  |   |      |        |        |    |
| Input capacitance   | C <sub>iss</sub>    | V <sub>GS</sub> = 0 V  | V <sub>DS</sub> = 25 V, f = 1 MHz               | -    | 10 810 | 14 500 | pF |
| Output capacitance  | C <sub>oss</sub>    |  |   | -    | 6500   | 8500   |    |
| Reverse transfer capacitance                                      | C <sub>rss</sub>    |  |   | -    | 700    | 950    |    |
| Total gate charge <sup>c</sup>                                    | Q <sub>g</sub>      | V <sub>GS</sub> = 10 V   | V <sub>DS</sub> = 20 V, I <sub>D</sub> = 10 A   | -    | 140    | 220    | nC |
| Gate-source charge <sup>c</sup>                                   | Q <sub>gs</sub>     |  |   | -    | 30     | -      |    |
| Gate-drain charge <sup>c</sup>                                    | Q <sub>gd</sub>     |  |   | -    | 20     | -      |    |
| Gate resistance   | R <sub>g</sub>      | f = 1 MHz  |   | 0.45 | 0.99   | 1.50   | Ω  |
| Turn-on delay time <sup>c</sup>                                   | t <sub>d(on)</sub>  | V <sub>DD</sub> = 20 V, R <sub>L</sub> = 2 Ω<br>I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω |   | -    | 24     | 40     | ns |
| Rise time <sup>c</sup>  | t <sub>r</sub>      |  |   | -    | 60     | 100    |    |
| Turn-off delay time <sup>c</sup>                                  | t <sub>d(off)</sub> |  |   | -    | 60     | 100    |    |
| Fall time <sup>c</sup>  | t <sub>f</sub>      |  |   | -    | 30     | 50     |    |
| <b>Source-Drain Diode Ratings and Characteristics<sup>b</sup></b> |                     |  |   |      |        |        |    |
| Pulsed current <sup>a</sup>                                       | I <sub>SM</sub>     |  |   | -    | -      | 200    | A  |
| Forward voltage   | V <sub>SD</sub>     | I <sub>F</sub> = 50 A, V <sub>GS</sub> = 0   |   | -    | 0.8    | 1.2    | V  |

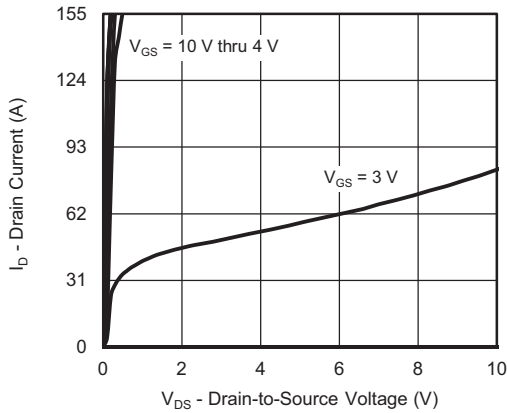
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %  
b. Guaranteed by design, not subject to production testing  
c. Independent of operating temperature

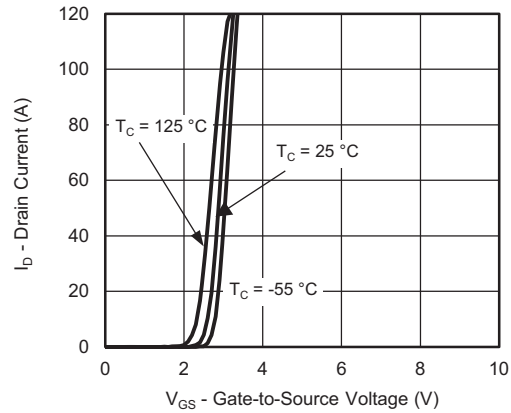
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



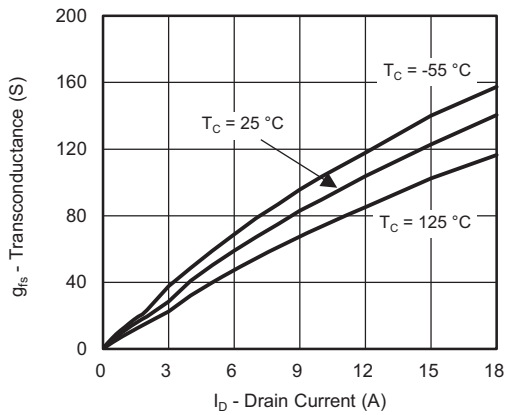
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



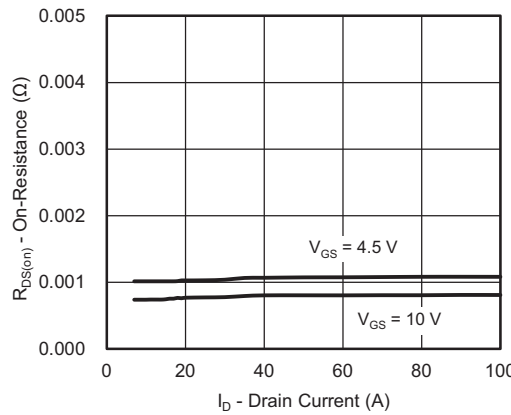
Output Characteristics



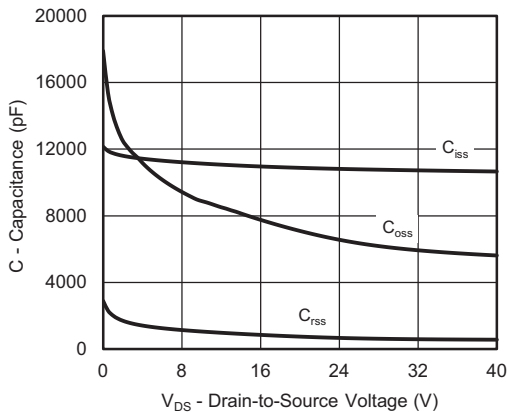
Transfer Characteristics



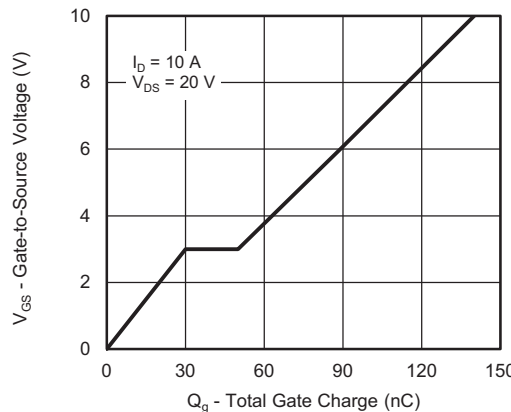
Transconductance



On-Resistance vs. Drain Current



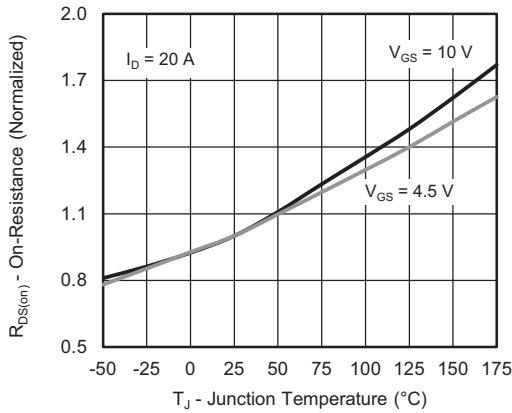
Capacitance



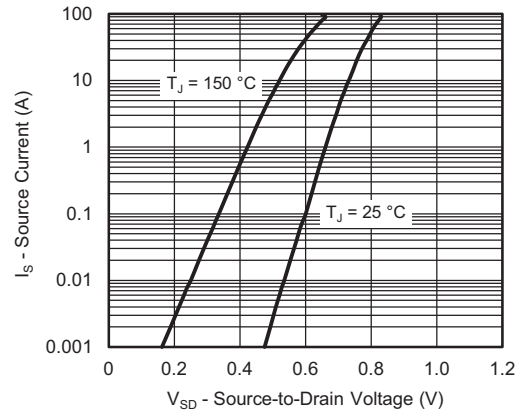
Gate Charge



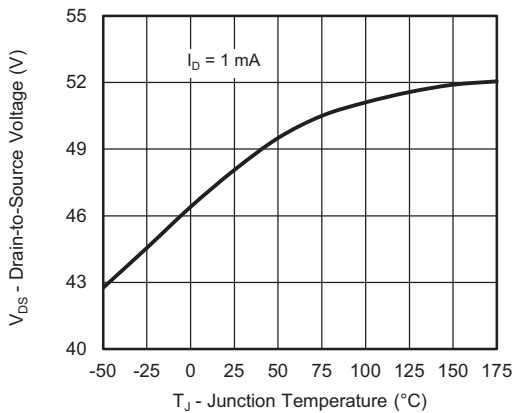
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



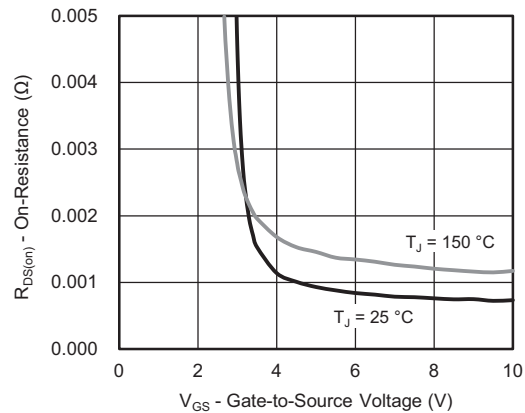
On-Resistance vs. Junction Temperature



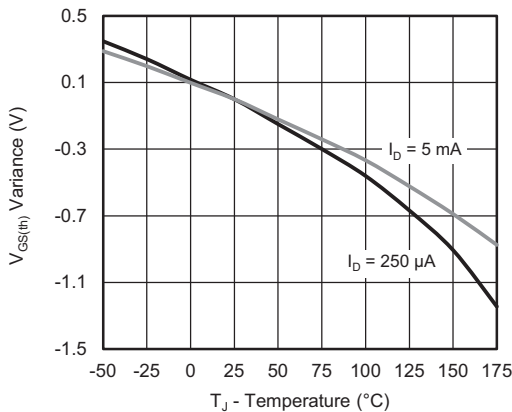
Source Drain Diode Forward Voltage



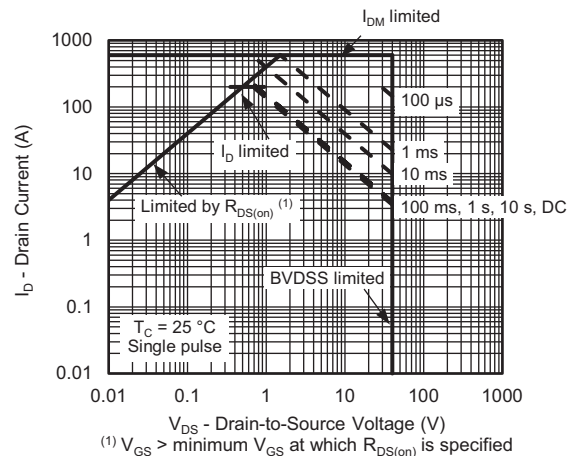
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



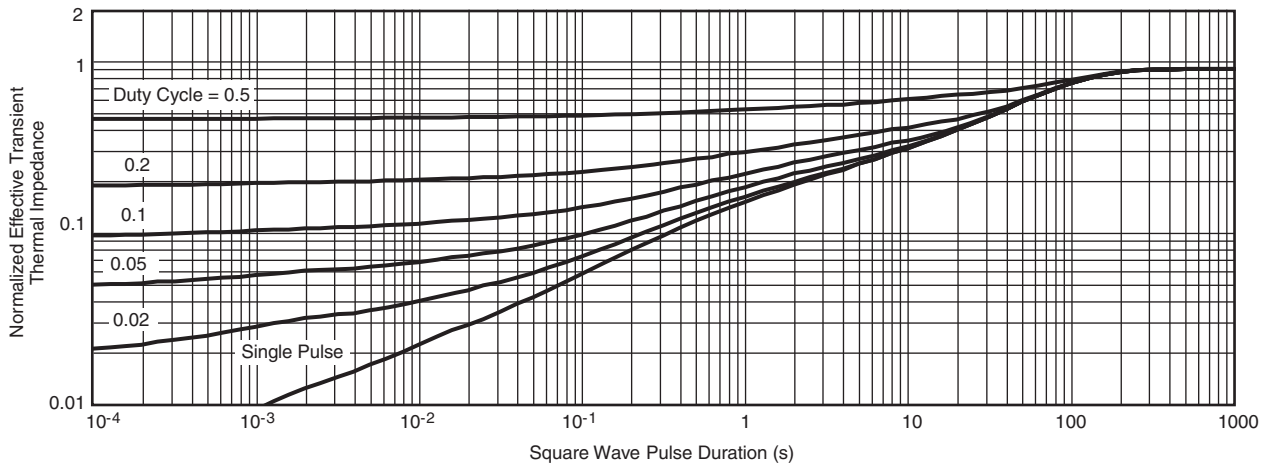
Threshold Voltage



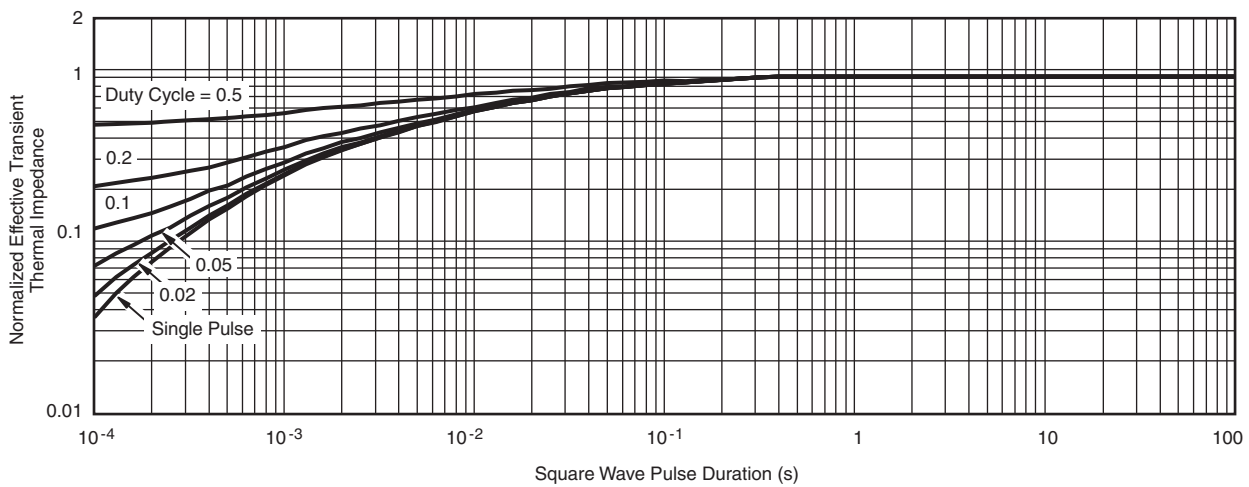
Safe Operating Area



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

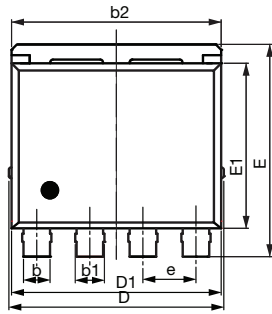


**Normalized Thermal Transient Impedance, Junction-to-Case**

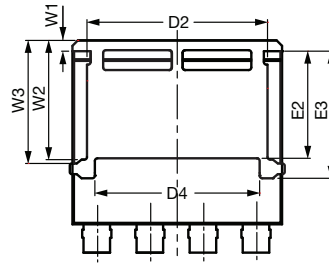
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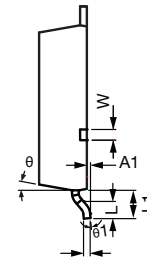
# PowerPAK® 8 x 8L Case Outline



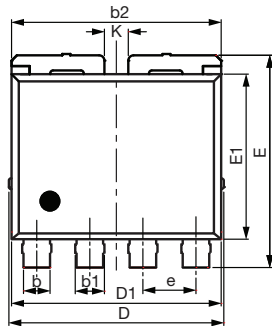
Top view (single)



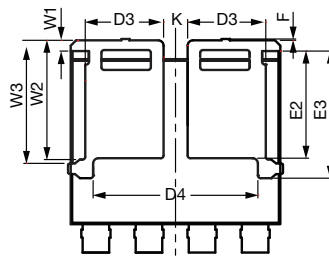
Bottom view (single)



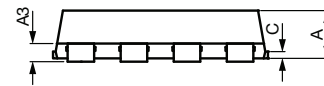
0.25 gauge line



Top view (dual)



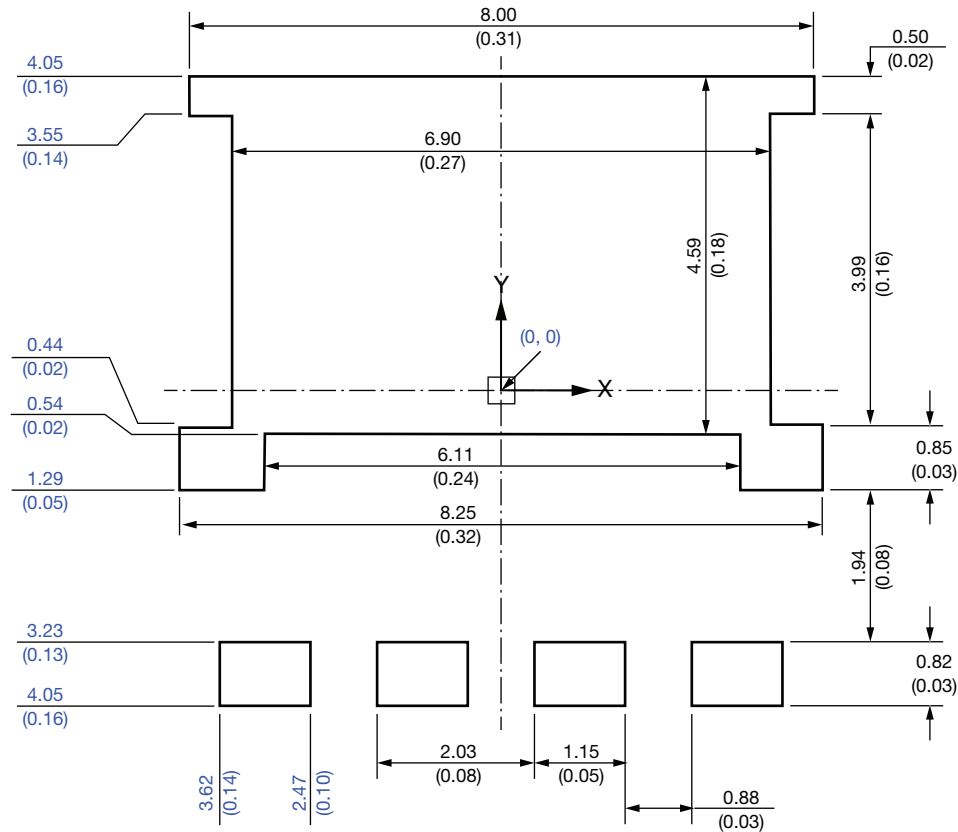
Bottom view (dual)



| DIM. | MILLIMETERS |      |      | INCHES |       |       |
|------|-------------|------|------|--------|-------|-------|
|      | MIN.        | NOM. | MAX. | MIN.   | NOM.  | MAX.  |
| A    | 1.70        | 1.80 | 1.90 | 0.067  | 0.071 | 0.075 |
| A1   | 0.00        | 0.08 | 0.13 | 0.000  | 0.003 | 0.005 |
| A3   | 0.55        | 0.62 | 0.70 | 0.022  | 0.024 | 0.028 |
| b    | 0.92        | 1.00 | 1.08 | 0.036  | 0.039 | 0.043 |
| b1   | 1.02        | 1.10 | 1.18 | 0.040  | 0.043 | 0.046 |
| b2   | 7.80        | 7.90 | 8.00 | 0.307  | 0.311 | 0.315 |
| c    | 0.20        | 0.25 | 0.30 | 0.008  | 0.010 | 0.012 |
| D    | 8.00        | 8.10 | 8.25 | 0.315  | 0.319 | 0.325 |
| D1   | 7.80        | 7.90 | 8.00 | 0.307  | 0.311 | 0.315 |
| D2   | 6.70        | 6.80 | 6.90 | 0.264  | 0.268 | 0.272 |
| D3   | 2.85        | 2.95 | 3.05 | 0.112  | 0.116 | 0.120 |
| D4   | 6.11        | 6.21 | 6.31 | 0.241  | 0.244 | 0.248 |
| e    | 1.95        | 2.00 | 2.05 | 0.077  | 0.079 | 0.081 |
| E    | 7.90        | 8.00 | 8.10 | 0.311  | 0.315 | 0.319 |
| E1   | 6.12        | 6.22 | 6.32 | 0.241  | 0.245 | 0.249 |
| E2   | 3.94        | 4.04 | 4.14 | 0.140  | 0.159 | 0.163 |
| E3   | 4.69        | 4.79 | 4.89 | 0.185  | 0.189 | 0.193 |
| F    | 0.05        | 0.10 | 0.15 | 0.002  | 0.004 | 0.006 |
| L    | 0.62        | 0.72 | 0.82 | 0.024  | 0.028 | 0.032 |
| L1   | 0.92        | 1.07 | 1.22 | 0.036  | 0.042 | 0.048 |
| K    | 0.80        | 0.90 | 1.00 | 0.031  | 0.035 | 0.039 |
| W    | 0.30        | 0.40 | 0.50 | 0.012  | 0.016 | 0.020 |
| W1   | 0.30        | 0.40 | 0.50 | 0.012  | 0.016 | 0.020 |
| W2   | 4.39        | 4.49 | 4.59 | 0.173  | 0.177 | 0.181 |
| W3   | 4.54        | 4.64 | 4.74 | 0.179  | 0.183 | 0.187 |
| θ    | 6°          | 10°  | 14°  | 6°     | 10°   | 14°   |
| θ1   | 0°          | 3°   | 8°   | 0°     | 3°    | 8°    |

C14-0891-Rev. A, 06-Oct-14  
DWG: 6026

## Recommended Minimum PADS for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

**Note**

- Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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